

IN THE SPECIFICATION:

Please rewrite the paragraphs appearing at page 3, line 1, through page 4, line 4, as follows:

--On a glass substrate 201, in each pixel, a gate electrode layer (lower electrode) 202, an insulation layer (amorphous silicon nitride film) 203, an amorphous silicon semiconductor layer 204, an amorphous n-silicon layer 205, and a source/drain electrode layer (upper electrode) 206 are laminated to constitute a selecting thin film transistor (TFT) 222. Also on the glass substrate, an extended portion (lower electrode) of the source/drain electrode layer 206, an amorphous p-silicon layer 207, an amorphous silicon semiconductor layer 208, an amorphous n-silicon layer 209 and an upper electrode layer 210 are laminated to constitute a photodiode 221. Further on the glass substrate 201, there is present a wiring portion 223 constituted by laminating the insulation layer 203, the amorphous silicon semiconductor layer 204, the amorphous n-silicon layer 205, and the source/drain electrode layer 206. Also a protective layer 211 constituted for example of an amorphous silicon nitride film is so formed as to cover these components, and a phosphor layer [[213]] (not shown) is adhered thereon by an adhesive layer 212. Such structure is described for example in Japanese Patent Application Laid-open No. H08-116044.

The phosphor layer [[213]] is provided for converting [[a]] incident radiation (X-rays) into [[a]] visible light. In general, a photodiode formed with amorphous silicon has an extremely low sensitivity to [[the]] X-rays. The phosphor layer [[213]] is constituted for example of a gadolinium-based material or [[a]] of CsI (cesium iodide).--